New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

1N645 thru 1N649
1N645A

Silicon General Purpose Diode

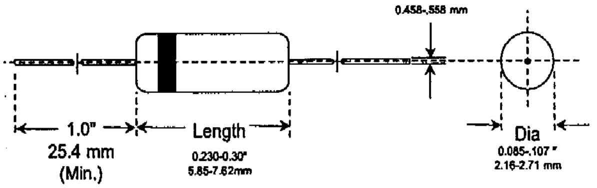
MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

	SYMBOL	1N645	1N645A	1N646	1N647	1N648	1N649	UNIT
Peak Working Reverse Voltage	V_{RWM}	225	225	300	400	500	600	V
Average Forward Current	I_O			400				mA
Average Forward Current (T_A=150°C)	I_O			150				mA
Peak Forward Surge Current	I_{FSM}			3.0				A
Power Dissipation	P_D			600				mW
Operating and Storage Junction Temperature	T_J, T_{stg}			-65 TO +175				°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

		1N645		1N645A		1N646		1N647		1N648		1N649		
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
I_R	V_R=V_{RWM}		0.2		0.2		0.2		0.2		0.2		0.2	µA
I_R	V_R=V_{RWM}, T_A=100°C		15		15		15		20		20		25	µA
I_R	V_R=60V		-		0.05		-		-		-		-	µA
I_R	V_R=60V, T_A=125°C		-		10		-		-		-		-	µA
V_F	I_F=400mA		1.0		1.0		1.0		1.0		1.0		1.0	V
C_T	V_R=12V, f=1.0MHz	5.0 TYP		5.0 TYP		5.0 TYP		5.0 TYP		5.0 TYP		5.0 TYP		pF

DO-7 Glass Package



Quality Semi-Conductors